

Schottky barrier diode

RB731U

●Applications

High speed switching.

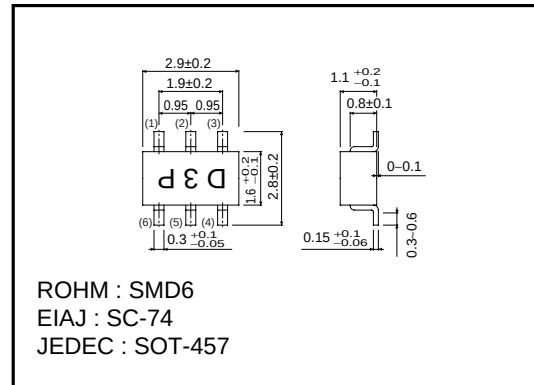
●Features

- 1) Small surface mounting type. (SMD6)
- 2) Low V_F and low I_R .
- 3) Three diodes in parallel for easy installation.

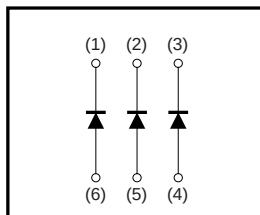
●Construction

Silicon epitaxial planar

●External dimensions (Unit : mm)



●Circuit



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	30	mA
Peak forward surge current*	I_{FSM}	200	mA
Junction temperature	T_J	125	°C
Storage temperature	T_{stg}	-40 to +125	°C

* 60 Hz for 1 ms

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	—	0.37	V	$I_F=1\text{mA}$
Reverse current	I_R	—	—	1	μA	$V_R=10\text{V}$
Capacitance between terminals	C_T	—	2.0	—	pF	$V_R=1\text{V}$, $f=1\text{MHz}$

Note) ESD sensitive product handling required.

Diodes

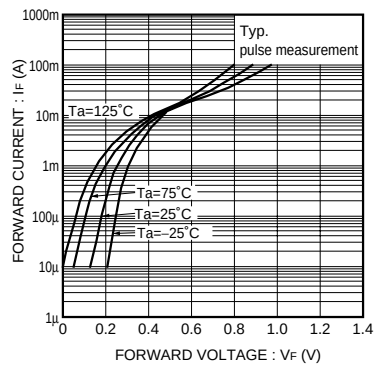
●Electrical characteristic curves ($T_a=25^\circ\text{C}$)

Fig.1 Forward characteristics

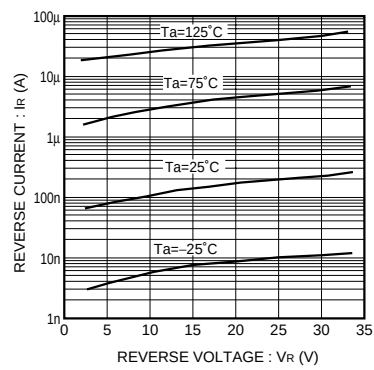


Fig.2 Reverse characteristics

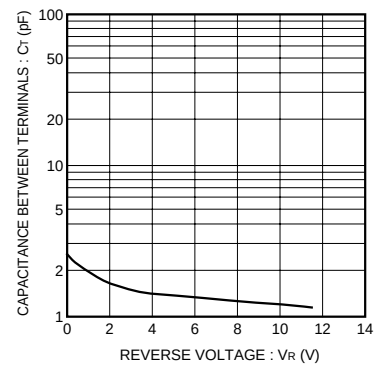
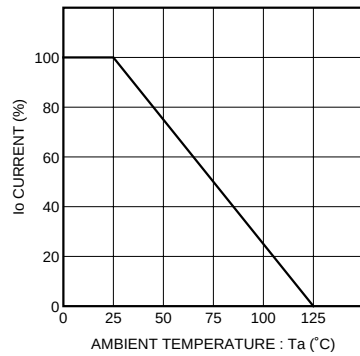


Fig.3 Capacitance between terminals characteristics

Fig.4 Derating curve
(mounting on glass epoxy PCBs)